## **Power MOSFET** 35V, 104mΩ, 3A, Single N-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

#### **Features**

- Low On-Resistance
- 4V drive
- Pb-Free, Halogen Free and RoHS compliance

#### **Typical Applications**

- Load Switch
- Motor Drive

#### **SPECIFICATIONS**

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	35	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ΙD	3	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	12	Α
Power Dissipation When mounted on ceramic substrate (900mm² × 0.8mm)	PD	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

- Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

  2 : This product is designed to "ESD immunity<200V\*", so please take care when
  - handling.
  - \*Machine Model

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm² × 0.8mm)	$R_{\theta JA}$	125	°C/W

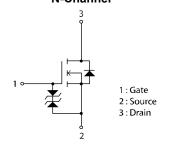


#### ON Semiconductor®

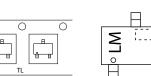
www.onsemi.com

VDSS	R <sub>DS</sub> (on) Max	ID Max	
	104mΩ@ 10V		
35V	173mΩ@ 4.5V	3A	
	208mΩ@ 4V		

#### **ELECTRICAL CONNECTION** N-Channel



#### **PACKING TYPE: TL**



**MARKING** 

#### **ORDERING INFORMATION**

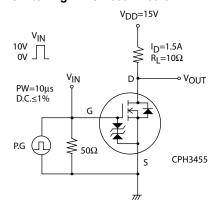
See detailed ordering and shipping information on page 5 of this data sheet.

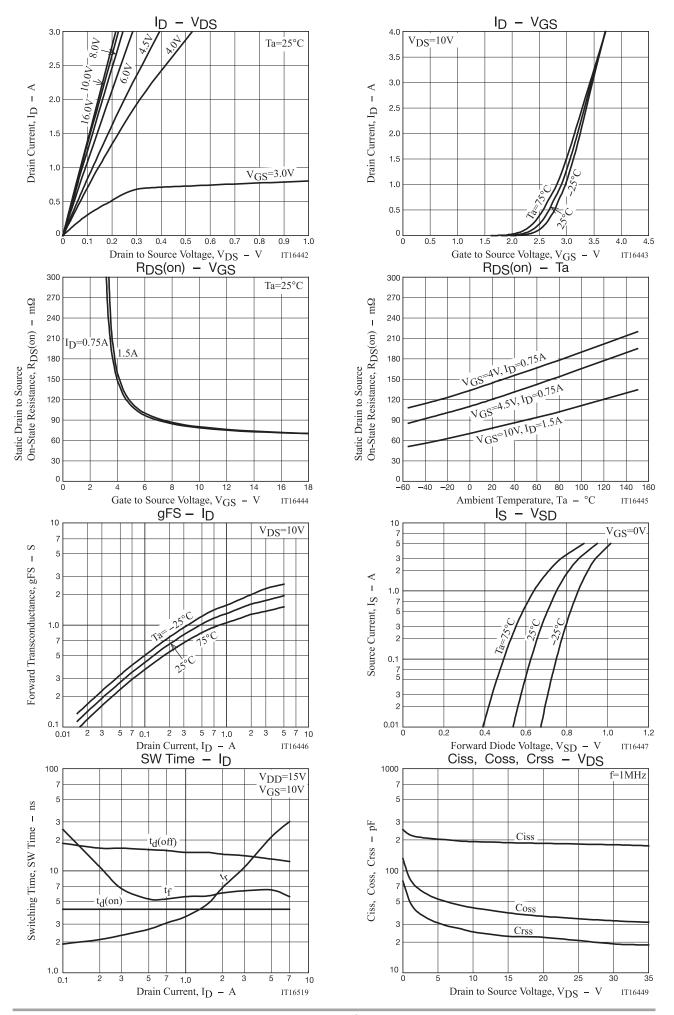
#### **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 3)

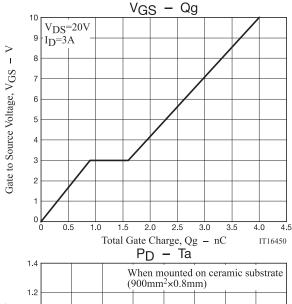
Parameter	Symbol	Conditions	Value			Unit
Farameter	Syllibol	Conditions	min	typ	max	Offic
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =35V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transconductance	gFS .	V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A		1.7		S
	R <sub>DS</sub> (on)1	I <sub>D</sub> =1.5A, V <sub>GS</sub> =10V		80	104	mΩ
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	ID=0.75A, VGS=4.5V		123	173	mΩ
Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.75A, V <sub>G</sub> S=4V		148	208	mΩ
Input Capacitance	Ciss			186		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		36		pF
Reverse Transfer Capacitance	Crss			22		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			4.2		ns
Rise Time	t <sub>r</sub>	On a supplified Took Observit		4.7		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		15		ns
Fall Time	tf			5.7		ns
Total Gate Charge	Qg			4		nC
Gate to Source Charge	Qgs	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A		0.9		nC
Gate to Drain "Miller" Charge	Qgd			0.7		nC
Forward Diode Voltage	V <sub>SD</sub>	IS=3A, VGS=0V		0.86	1.2	V

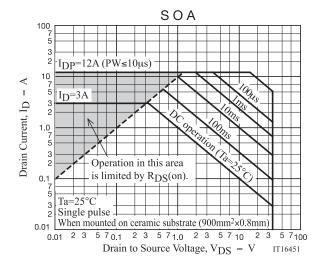
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

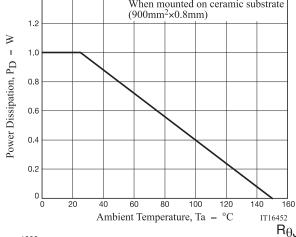
#### **Switching Time Test Circuit**

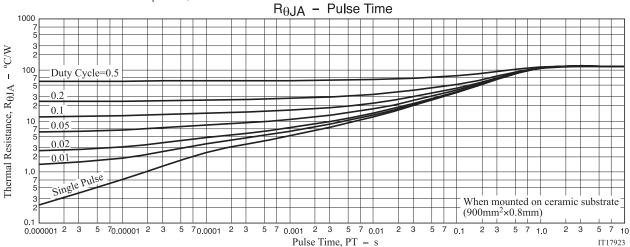






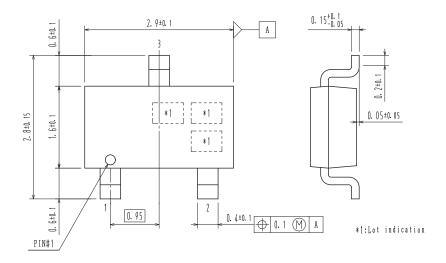






#### PACKAGE DIMENSIONS

unit: mm CPH3 CASE 318BA ISSUE O



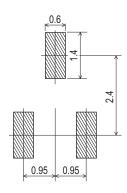
# 0.0 4±0.05

1 : Gate

2 : Source

3: Drain

#### Recommended Soldering Footprint



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing)	
CPH3455-TL-H	LM	CPH3 SC-59, SOT-23, TO-236	3,000 / Tape & Reel	
CPH3455-TL-W	LIVI	(Pb-Free / Halogen Free)		

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the CPH3455 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent re